

All electrical determination of Rashba and Dresselhaus spin-orbit interactions in InGaAs narrow wires

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In the field of spintronics, electrical control of spin and enhancement of spin lifetime are prerequisite techniques. In III-V semiconductor heterostructures, when strengths of two spin-orbit interactions (SOI), the Rashba SOI α and the Dresselhaus SOI β are equal to each other, coherent spin propagation is realized and spin relaxation due to the D'yakonov-Perel' mechanism is completely suppressed [1]. This is the so-called persistent spin helix (PSH) state [2]. To realize and apply the PSH state, the electrical determination of α and β in a gated sample is essential. In this study, we have successfully evaluated the absolute value of α and β .

A sample used was an $\text{In}_{0.52}\text{Al}_{0.48}\text{As} / \text{In}_{0.7}\text{Ga}_{0.3}\text{As} / \text{In}_{0.52}\text{Al}_{0.48}\text{As}$ quantum well, which was epitaxially grown on InP substrate and processed into narrow wire structures (Length $L = 200 \mu\text{m}$, Width $W = 750 \text{ nm}$, Number of wires $N = 100$) aligned in [100] direction. We measured out-plane magneto-conductance called weak localization (WL) (Fig. 1a) by varying an in-plane magnetic field $|\mathbf{B}_{\text{in}}|$ at $T = 1.7 \text{ K}$.

The method to deduce the SOI parameters is based on the theoretical proposal that the WL exhibits minimum amplitude with maximum spin relaxation rate when the in-plane magnetic field $|\mathbf{B}_{\text{in}}|$ is very close to the effective magnetic field $|\mathbf{B}_{\text{eff}}|$ induced by two SOIs [3]. We experimentally observe the $|\mathbf{B}_{\text{in}}|$ dependence of the 'difference of the WL amplitudes $G' = \Delta\sigma(\theta \neq 0^\circ) - \Delta\sigma(\theta = 0^\circ)$ ' at $V_g = -5 \text{ V}$ (Carrier density $N_s = 2.16 \times 10^{12} \text{ cm}^{-2}$), where $\Delta\sigma$ is a WL amplitude and θ is the angle between \mathbf{B}_{in} and \mathbf{B}_{eff} (Fig. 1b). $|G'|$ corresponds to how much WL amplitude is suppressed by the additional spin relaxation, which becomes maximum at dip position with the ratio $|\mathbf{B}_{\text{in}}|/|\mathbf{B}_{\text{eff}}| \approx 1$. From the dip position in Fig. 1b, we estimate $|\mathbf{B}_{\text{eff}}| \approx 1.55 \text{ T}$. Moreover, using the estimated $|\mathbf{B}_{\text{eff}}|$ values together with the ratio α/β deduced by our proposed method [3], it is possible to evaluate the absolute values of α and β .

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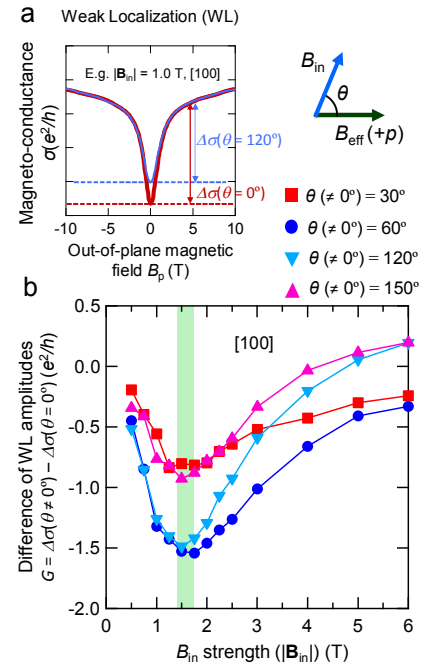


Figure 1: a. measured WL in [100] direction with $|\mathbf{B}_{\text{in}}| = 1 \text{ T}$ in different θ . b. The difference of WL amplitudes $G' = \Delta\sigma(\theta \neq 0^\circ) - \Delta\sigma(\theta = 0^\circ)$ as a function of $|\mathbf{B}_{\text{in}}|$. Each angle $\theta \neq 0^\circ$ was set as $\theta = 30^\circ, 60^\circ, 120^\circ$ and 150° .